

		Search Text	Des	Time Stamp
Bits	Text			Time Stamp
1	215	esd with buried	US-EPUS; USPAT; 2004/08/17	BR
2	319	esd same (under or below) with pad	EPO; JPO; DERVENT; 11:18	IBM,IND.
3	41456	vias with resistance	US-EPUS; USPAT; 2004/08/17	BR
4	1857	vias with resistance with parallel	EPO; JPO; DERVENT; 11:19	IBM,IND.
5	9148	257/173,355.cc15. 361/90,91,91.1-91.8,FOR100.cc15.	US-EPUS; USPAT; 2004/08/17	BR
6	258	esd and (resistance or resistor) and (transistor same below same pad)	EPO; JPO; DERVENT; 11:59	IBM,IND.
7	4148	257/173,355.cc15. 361/90,91,91.1-91.8,FOR100.cc15.	US-EPUS; USPAT; 2004/08/17	BR
8	44	(257/173,355.cc15. 361/90,91,91.1-91.8,FOR100.cc15.) and (esd with buried)	EPO; JPO; DERVENT; 11:38	IBM,IND.
9	28	(257/173,355.cc15. 361/90,91,91.1-91.8,FOR100.cc15.) and (esd with buried) and pad	US-EPUS; USPAT; 2004/08/17	BR
10	16	((257/173,355.cc15. 361/90,91,91.1-91.8,FOR100.cc15.) and (esd with buried)) not ((257/173,355.cc15. 361/90,91,91.1-91.8,FOR100.cc15.) and (esd with buried)) and (esd with buried) and pad	EPO; JPO; DERVENT; 11:39	IBM,IND.
11	25	(esd same (under or below) with pad) and (257/173,355.cc15. 361/90,91,91.1-91.8,FOR100.cc15.)	US-EPUS; USPAT; 2005/01/12	BR
12	93	((esd same (under or below) with pad) and (257/173,355.cc15. 361/90,91,91.1-91.8,FOR100.cc15.) and (esd with buried)) not ((257/173,355.cc15. 361/90,91,91.1-91.8,FOR100.cc15.) and (esd with buried)) and (esd with buried) and pad)	EPO; JPO; DERVENT; 11:09	IBM,IND.
13	58	esd and (resistance or resistor) and (transistor same below same pad) and (257/173,355.cc15. 361/90,91,91.1-91.8,FOR100.cc15.)	US-EPUS; USPAT; 2005/01/12	IBM,IND.
14	5	(257/173,355.cc15. 361/90,91,91.1-91.8,FOR100.cc15.) and (esd with buried) and #pd>"20040817"	EPO; JPO; DERVENT; 11:09	IBM,IND.
15	4	(257/173,355.cc15. 361/90,91,91.1-91.8,FOR100.cc15.) and (esd with buried) and pad and #pd>"20040817"	US-EPUS; USPAT; 2005/01/12	BR
16	1	((257/173,355.cc15. 361/90,91,91.1-91.8,FOR100.cc15.) and (esd with buried)) not ((257/173,355.cc15. 361/90,91,91.1-91.8,FOR100.cc15.) and (esd with buried)) and (esd with buried) and pad	US-EPUS; USPAT; 2005/01/12	IBM,IND.
17	6	(esd same (under or below) with pad) and (257/173,355.cc15. 361/90,91,91.1-91.8,FOR100.cc15.) and #pd>"20040817"	US-EPUS; USPAT; 2005/01/12	BR
18	6	((esd same (under or below) with pad) and (257/173,355.cc15. 361/90,91,91.1-91.8,FOR100.cc15.) and (esd with buried)) not ((257/173,355.cc15. 361/90,91,91.1-91.8,FOR100.cc15.) and (esd with buried)) and (esd with buried) and pad	US-EPUS; USPAT; 2005/01/12	IBM,IND.
19	6	(esd and (resistance or resistor) and (transistor same below same pad)) and (257/173,355.cc15. 361/90,91,91.1-91.8,FOR100.cc15.) and #pd>"20040817"	US-EPUS; USPAT; 2005/01/12	BR
20	14	514 515 516 517 518 519	EPO; JPO; DERVENT; 11:10	IBM,IND.
21	2	#6762466-.pn	EPO; JPO; DERVENT; 11:26	IBM,IND.
22	0	#10759173"	EPO; JPO; DERVENT; 13:59	IBM,IND.

updated EAST 6/30/05